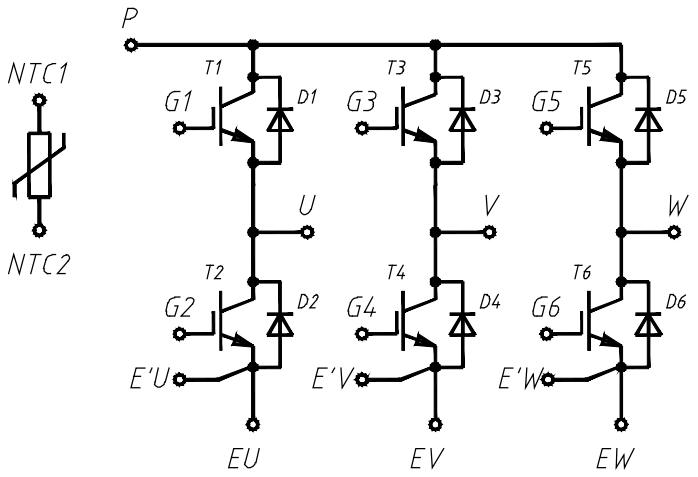
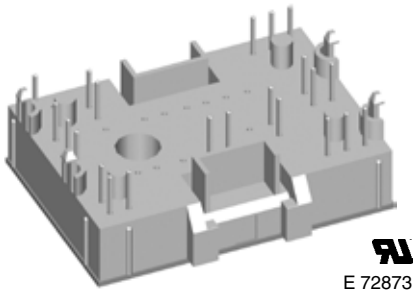
Six-Pack
XPT IGBT

V_{CES} = 1200 V
I_{C25} = 43 A
$V_{CE(sat)}$ = 1.8 V

Part name (Marking on product)

MIXA30W1200TMH





E 72873

Pin configuration see outlines.

Features:

- High level of integration - only one power semiconductor module required for the whole drive
- Rugged XPT design (Xtreme light Punch Through) results in:
  - short circuit rated for 10 µsec.
  - very low gate charge
  - square RBSOA @ 3x I_C
  - low EMI
- Thin wafer technology combined with the XPT design results in a competitive low $V_{CE(sat)}$
- Temperature sense included
- SONIC™ diode
  - fast and soft reverse recovery
  - low operating forward voltage

Application:

- AC motor drives
- Pumps, Fans
- Washing machines
- Air-conditioning system
- Inverter and power supplies

Package:

- "Mini" package
- Assembly height is 17 mm
- Insulated base plate
- Pins suitable for wave soldering and PCB mounting
- Assembly clips available
  - IXKU 5-505 screw clamp
  - IXRB 5-506 click clamp
- UL registered E72873

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Ouput Inverter T1 - T6

Symbol	Definitions	Conditions		Ratings min.	typ.	max.	Unit
V_{CES}	*collector emitter voltage*		T_{VJ} = 25°C			1200	V
V_{GES}	*max. DC gate voltage*	continuous				±20	V
V_{GEM}	*max. transient collector gate voltage*	transient				±30	V
I_{C25}	*collector current*		T_C = 25°C			43	A
I_{C80}			T_C = 80°C			30	A
P_{tot}	*total power dissipation*		T_C = 25°C			150	W
$V_{CE(sat)}$	*collector emitter saturation voltage*	I_C = 25 A; V_{GE} = 15 V	T_{VJ} = 25°C		1.8	2.1	V
			T_{VJ} = 125°C		2.1		V
$V_{GE(th)}$	*gate emitter threshold voltage*	I_C = 1 mA; V_{GE} = V_{CE}	T_{VJ} = 25°C	5.4	5.9	6.5	V
I_{CES}	*collector emitter leakage current*	V_{CE} = V_{CES}; V_{GE} = 0 V	T_{VJ} = 25°C		0.02	0.15	mA
			T_{VJ} = 125°C		0.3		mA
I_{GES}	*gate emitter leakage current*	V_{GE} = ±20 V				500	nA
$Q_{G(on)}$	*total gate charge*	V_{CE} = 600 V; V_{GE} = 15 V; I_C = 25 A			76		nC
$t_{d(on)}$	*turn-on delay time*	inductive load V_{CE} = 600 V; I_C = 25 A V_{GE} = ±15 V; R_G = 39 Ω	T_{VJ} = 125°C		70		ns
t_r	*current rise time*				40		ns
$t_{d(off)}$	*turn-off delay time*				250		ns
t_f	*current fall time*				100		ns
E_{on}	*turn-on energy per pulse*				2.5		mJ
E_{off}	*turn-off energy per pulse*				3.0		mJ
RBSOA	*reverse bias safe operating area*	V_{GE} = ±15 V; R_G = 39 Ω; V_{CEK} = 1200 V	T_{VJ} = 125°C			75	A
I_{SC} **(SCSOA)**	*short circuit safe operating area*	V_{CE} = 900 V; V_{GE} = ±15 V; R_G = 39 Ω; t_p = 10 µs; non-repetitive	T_{VJ} = 125°C		100		A
R_{thJC}	*thermal resistance junction to case*	(per IGBT)				0.84	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.24		K/W

Output Inverter D1 - D6

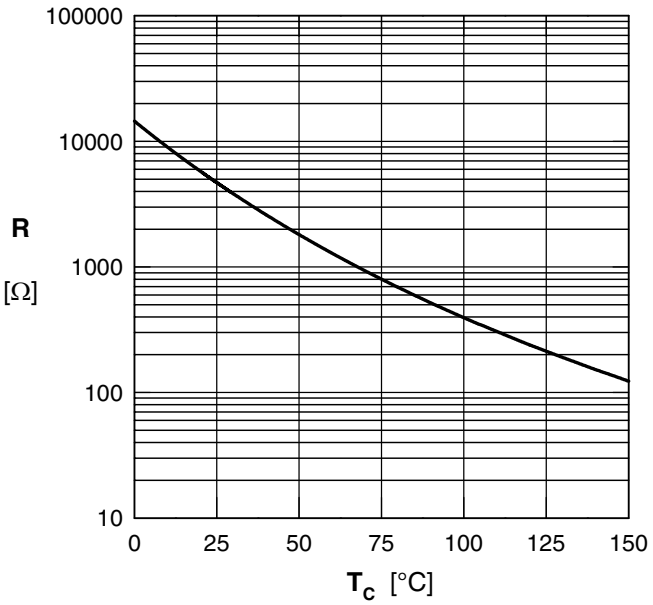
Symbol	Definitions	Conditions		Ratings min.	typ.	max.	Unit
V_{RRM}	*max. repetitve reverse voltage*		T_{VJ} = 25°C			1200	V
I_{F25}	*forward current*		T_C = 25°C			44	A
I_{F80}			T_C = 80°C			29	A
V_F	*forward voltage*	I_F = 30 A; V_{GE} = 0 V	T_{VJ} = 25°C		1.95	2.2	V
			T_{VJ} = 125°C		1.95		V
Q_{rr}	*reverse recovery charge*	V_R = 600 V di_F/dt = -600 A/µs I_F = 30 A; V_{GE} = 0 V	T_{VJ} = 125°C		3.5		µC
I_{RM}	*max. reverse recovery current*				30		A
t_{rr}	*reverse recovery time*				350		ns
E_{rec}	*reverse recovery energy*				0.9		mJ
R_{thJC}	*thermal resistance junction to case*	(per diode)				1.2	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.4		K/W

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Temperature Sensor NTC

Symbol	Definitions	Conditions	Ratings min.	typ.	max.	Unit
R_{25}	*resistance*	T_C = 25°C	4.75	5.0	5.25	kΩ
$B_{25/50}$				3375		K



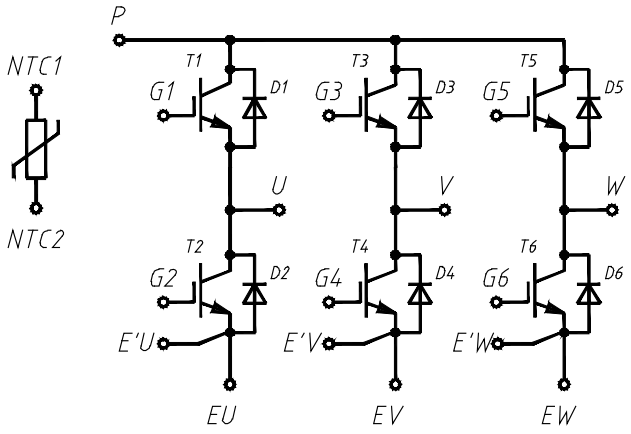
Typ. NTC resistance vs. temperature

Module

Symbol	Definitions	Conditions	Ratings min.	typ.	max.	Unit
T_{VJ}	*operating temperature*		-40		125	°C
T_{VJM}	*max. virtual junction temperature*				150	°C
T_{stg}	*storage temperature*		-40		125	°C
V_{ISOL}	*isolation voltage*	$I_{ISOL} \leq$ 1 mA; 50/60 Hz			2500	V~
CTI	*comparative tracking index*				-	
F_C	*mounting force*		40		80	N
d_S	*creep distance on surface*		12.7			mm
d_A	*strike distance through air*		12			mm
Weight				35		g

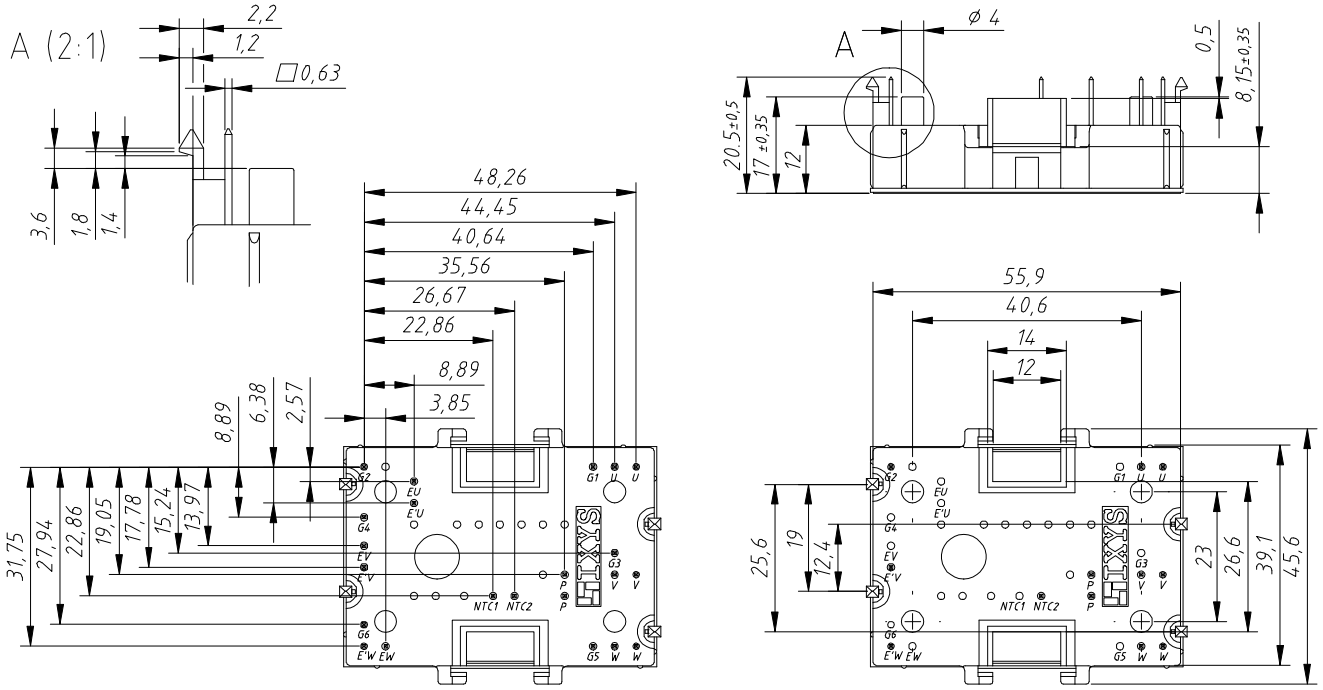
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Circuit Diagram



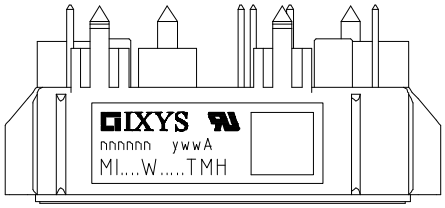
Outline Drawing

Dimensions in mm (1 mm = 0.0394“)



Bemerkungen:
1) Toleranz für Pin Positionen entsprechend ⌖ ∅ 0.4
2) Vorgesehen für die Montage auf Leiterplatten mit einer Dicke von 1.6 ±0.2 mm

Remarks:
1.) pin positions with tolerance ⌖ ∅ 0.4
2) mounting on PCB with thickness of 1.6 ±0.2 mm



Part number

M = Module
I = IGBT
X = XPT
A = standard
30 = Current Rating [A]
W = 6-Pack
1200 = Reverse Voltage [V]
T = NTC
MH = MiniPack2

Ordering	Part Number	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MIXA 30 W 1200 TMH	MIXA30W1200TMH	Box	20	470414

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20101102b

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IGBT T1 - T6

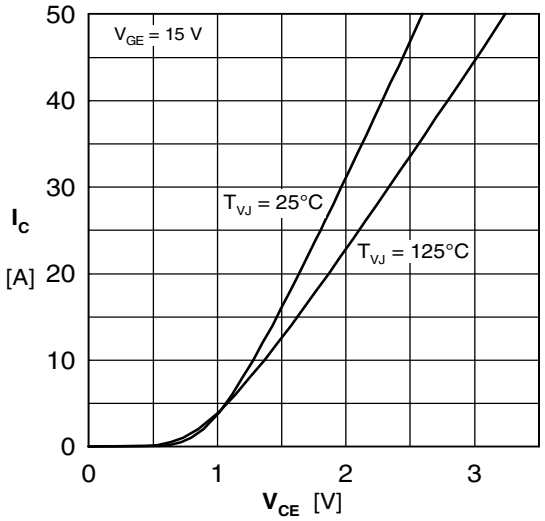


Fig. 1 Typ. output characteristics

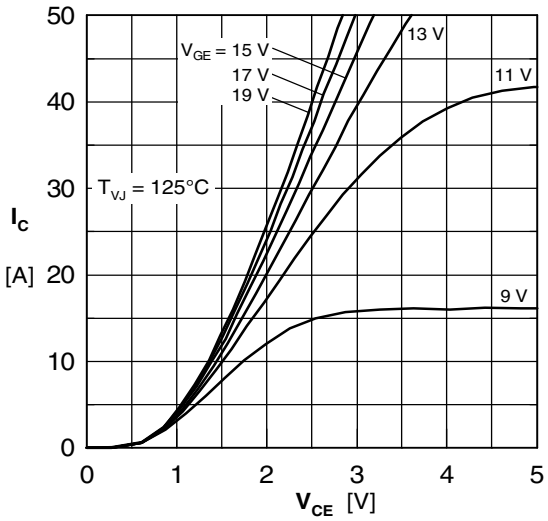


Fig. 2 Typ. output characteristics

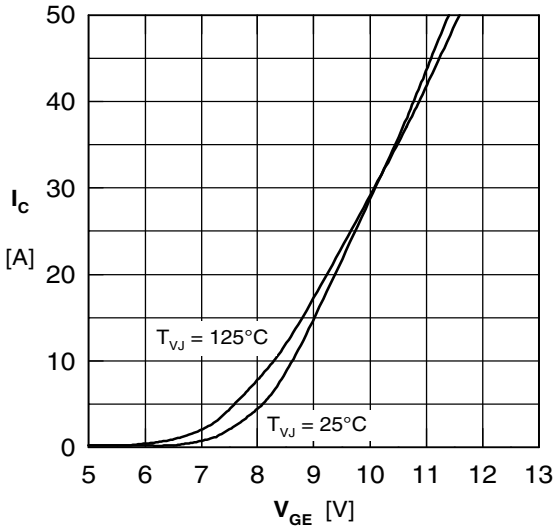


Fig. 3 Typ. tranfer characteristics

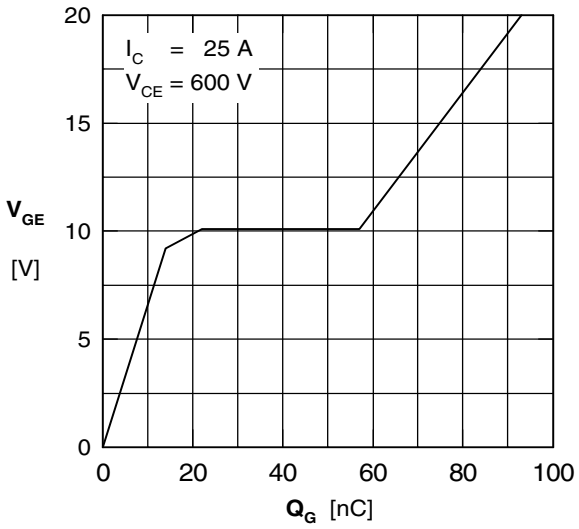


Fig. 4 Typ. turn-on gate charge

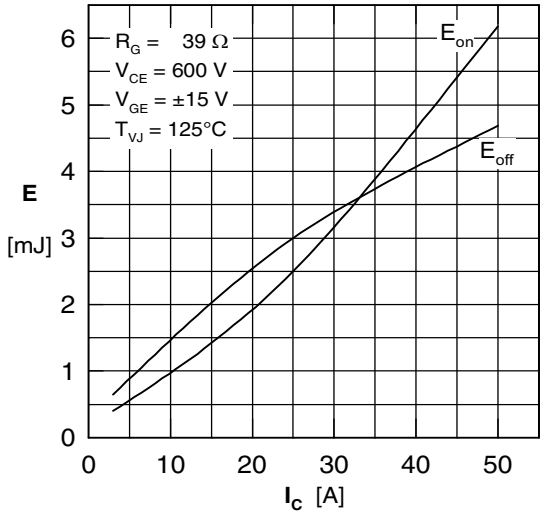


Fig. 5 Typ. switching energy vs. collector current

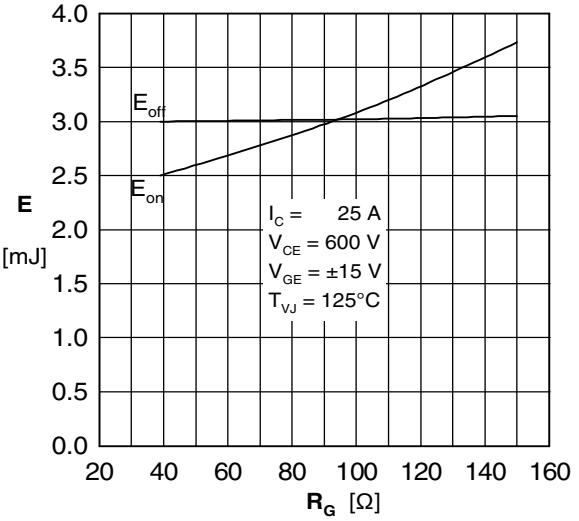


Fig. 6 Typ. switching energy vs. gate resistance

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Diode D1 - D6

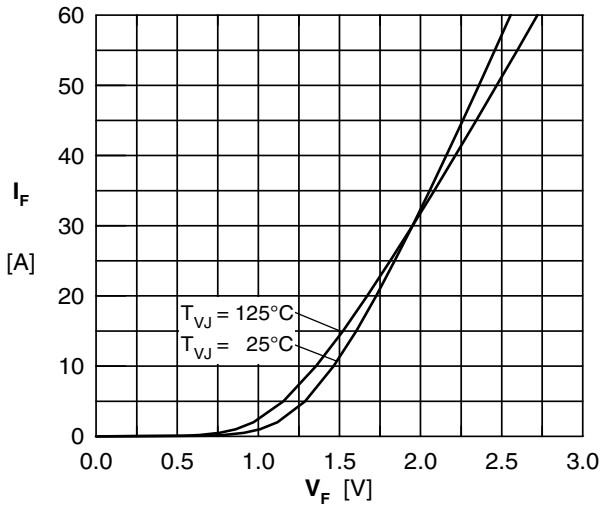


Fig. 7 Typ. Forward current versus V_F

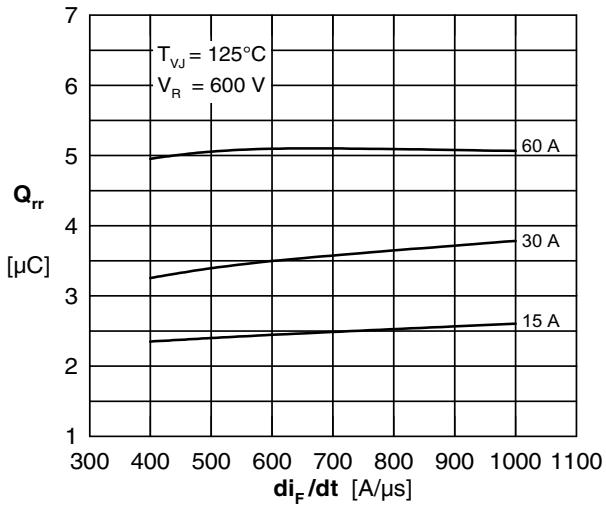


Fig. 8 Typ. reverse recov.charge Q_{rr} vs. di/dt

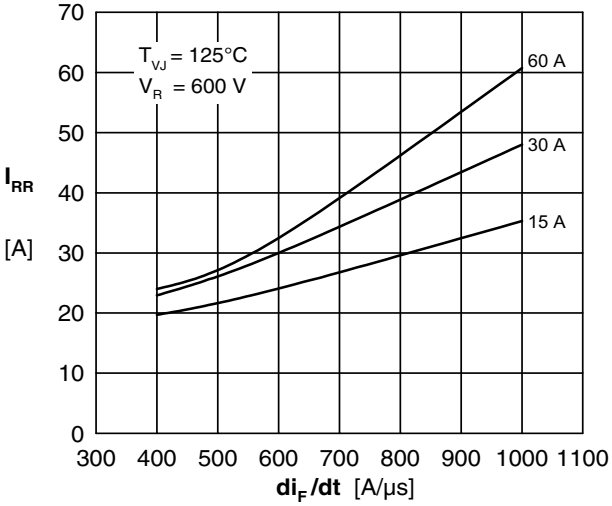


Fig. 9 Typ. peak reverse current I_{RM} vs. di/dt

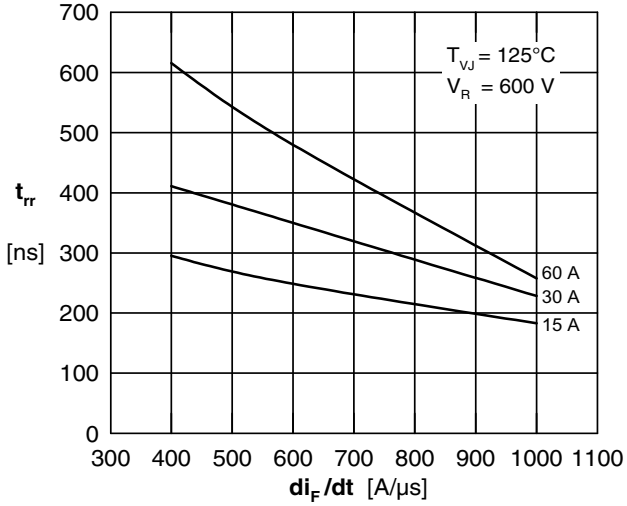


Fig. 10 Typ. recovery time t_{rr} versus di/dt

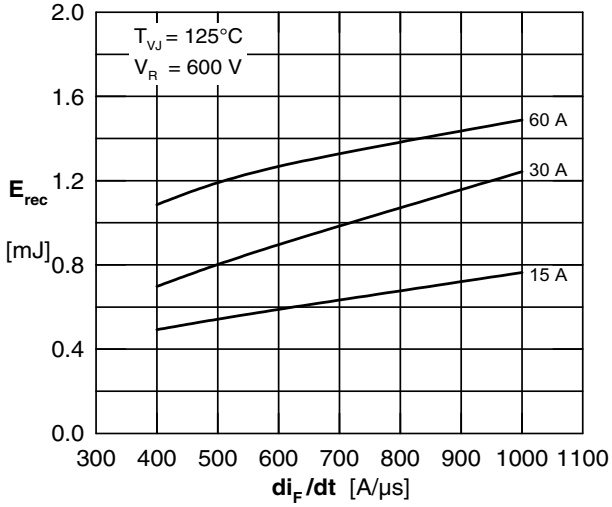
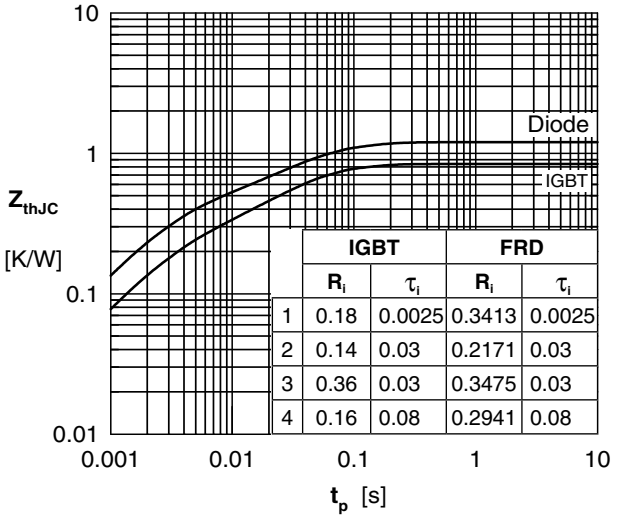


Fig.11 Typ. recovery energy E_{rec} versus di/dt



	IGBT		FRD	
	R_i	τ_i	R_i	τ_i
1	0.18	0.0025	0.3413	0.0025
2	0.14	0.03	0.2171	0.03
3	0.36	0.03	0.3475	0.03
4	0.16	0.08	0.2941	0.08

Fig. 12 Typ. transient thermal impedance

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